New Jersey Semi-Conductor Products, Inc.

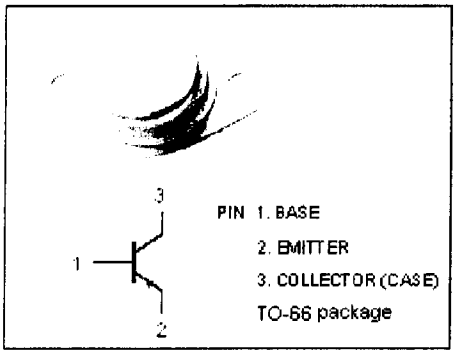
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2N5611

DESCRIPTION

- DC Current Gain-
  : h_{FE}= 30-90@I_C= -2.5A
- Wide Area of Safe Operation
- Collector-Emitter Sustaining Voltage-
  : $V_{CEO(SUS)}$= -100V(Min)
- Complement to Type 2N5612



APPLICATIONS

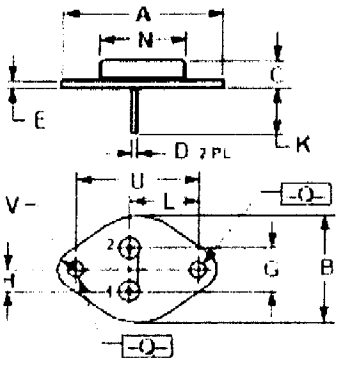
- Designed for use in high frequency power amplifiers, audio power amplifier and drivers.

ABSOLUTE MAXIMUM RATINGS(T_a=25℃)

SYMBOL	PARAMETER	VALUE	UNIT
V_{CBO}	Collector-Base Voltage	-120	V
V_{CEO}	Collector-Emitter Voltage	-100	V
V_{EBO}	Emitter-Base Voltage	-6	V
I_C	Collector Current-Continuous	-5	A
P_C	Collector Power Dissipation@T_C=25℃	25	W
T_J	Junction Temperature	150	℃
T_{stg}	Storage Temperature	-65~150	℃

THERMAL CHARACTERISTICS

SYMBOL	PARAMETER	MAX	UNIT
$R_{th\ j\text{-}c}$	Thermal Resistance,Junction to Case	6.0	℃/W



DIM	mm	
	MIN	MAX
A	31.40	31.80
B	17.30	17.70
C	6.70	7.10
D	0.70	0.90
E	1.40	1.60
G	5.08	
H	2.54	
K	9.80	10.20
L	14.70	14.90
N	12.40	12.60
Q	3.60	3.80
U	24.30	24.50
V	3.60	3.70

NJ Semi-Conductors reserves the right to change test conditions, parameters limits and package dimensions without notice information furnished by NJ Semi-Conductors is believed to be both accurate and reliable at the time of going to press. However NJ Semi-Conductors assumes no responsibility for any errors or omissions discovered in its use. NJ Semi-Conductors encourages customers to verify that datasheets are current before placing orders.

Quality Semi-Conductors

ELECTRICAL CHARACTERISTICS

T_C=25℃ unless otherwise specified

SYMBOL	PARAMETER	CONDITIONS	MIN	MAX	UNIT
$V_{CEO(SUS)}$	Collector-Emitter Sustaining Voltage	I_C= -50mA ; I_B= 0	-100		V
$V_{CE(sat)}$	Collector-Emitter Saturation Voltage	I_C= -2.5A; I_B= -0.25A		-0.75	V
$V_{BE(sat)}$	Base-Emitter Saturation Voltage	I_C= -2.5A; I_B= -0.25A		-1.45	V
I_{CEO}	Collector Cutoff Current	V_{CE}= -100V; I_B= 0		-1.0	mA
I_{CBO}	Collector Cutoff Current	V_{CB}= -120V; I_E= 0		-0.1	mA
I_{EBO}	Emitter Cutoff Current	V_{EB}= -6V; I_C= 0		-0.1	mA
h_{FE}	DC Current Gain	I_C= -2.5A ; V_{CE}= -5V	30	90	
f_T	Current-Gain—Bandwidth Product	I_C= -0.5A ; V_{CE}= -10V	50		MHz